

S/N 08/902,133

PATENT

# 21/10  
7/11/2000  
AMW

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Leonard Forbes et al.

Examiner: George C. Eckert II

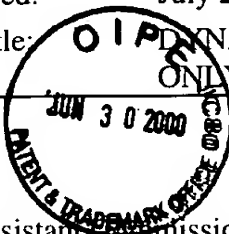
Serial No.: 08/902,133

Group Art Unit: 2815

Filed: July 29, 1997

Docket: 303.356US1

Title: **ADAPTIVE DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE**



**AMENDMENT AND RESPONSE**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Applicant has reviewed the Office Action dated 28 March 2000. Please amend the application as follows:

**IN THE SPECIFICATION**

Please delete lines 6-18 of page 1 of the original specification, beginning with the heading "**Cross Reference To Related Applications**".

**IN THE CLAIMS**

Please amend the claims as follows:

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sub E117  
29. (Twice Amended) A memory cell comprising:  
a storage electrode to store charge;  
a control electrode[,] separated from [a] the storage electrode by an intergate dielectric;  
and  
wherein the intergate dielectric has a permittivity that is higher than a permittivity of silicon dioxide.

sub E1147  
66. (Amended) The memory device of claim 65 wherein:  
the barrier energy between the floating gate and the insulator is less than approximately 2.0 eV;  
the insulator comprises a material that has a larger electron affinity than silicon dioxide;  
the floating gate comprises a material that has a smaller electron affinity than polycrystalline silicon; [and]

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01 FC:103  
02 FC:102

108.00 OP

234.00 OP